

CHAPTER FIVE

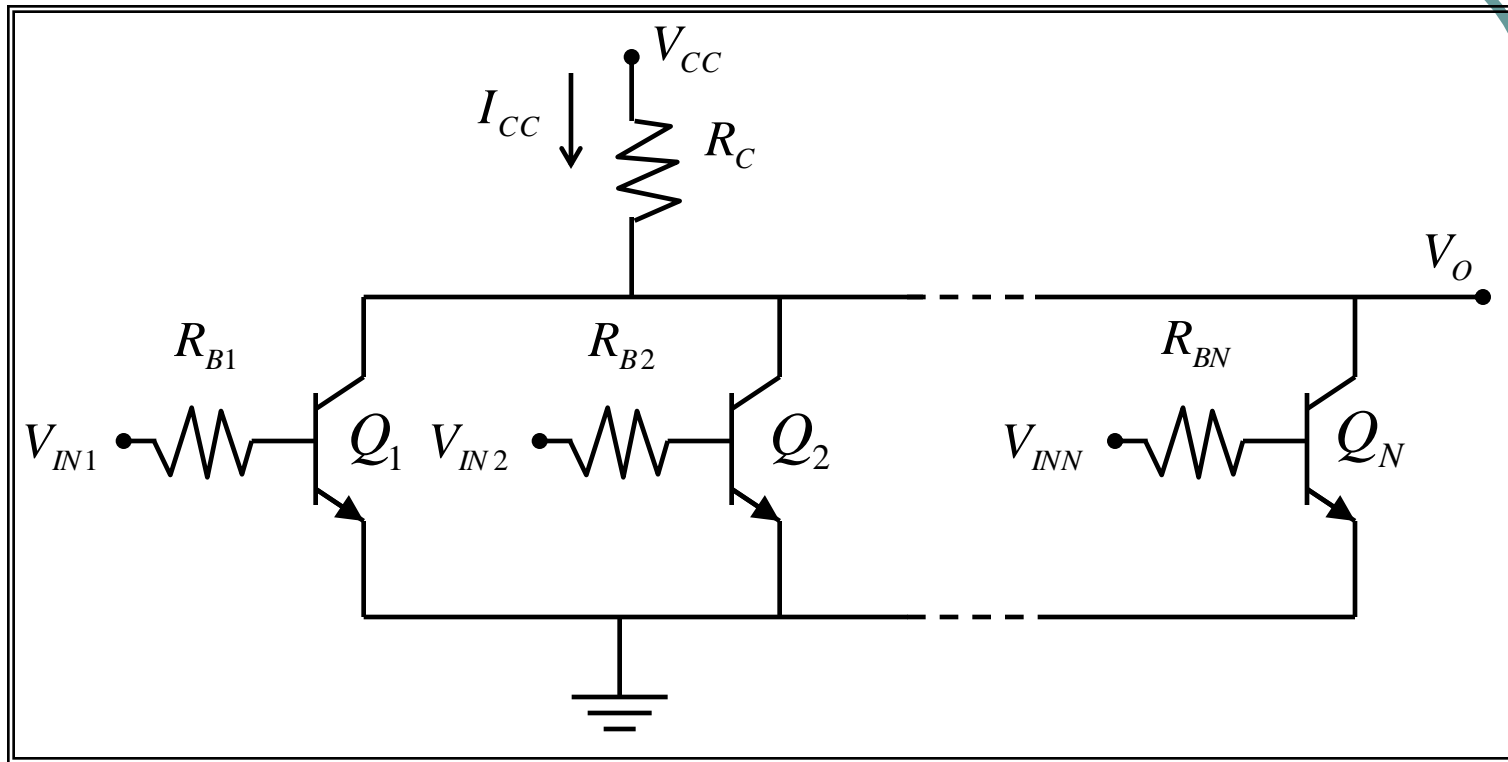
RTL NOR Gate

Digital Electronics.

Introduction

- RTL Inverter: discussed in Ch.4 ✓
- RTL NOR gate
- RTL NAND gate
- RTL OR gate
- RTL AND gate

Basic RTL NOR Gate



$$I_{CC} = \sum_{n=1}^N I_{Cn}$$

$$V_O = V_{CC} - I_{CC}R_C$$

If all inputs are less than $V_{BE}(FA)$ $\rightarrow V_O = V_{CC}$

If at least one input is greater than V_{IH} $\rightarrow V_O = V_{CE}(sat)$

High
Low

Basic RTL NAND Gate

Assuming $\beta_F \gg 1$, I_B is negligible to I_C

$$I_{CC} = I_{C1} \cong I_{E1} \cong I_{E2}$$

$$V_O = V_{CC} - I_{CC}R_C$$

If at least one input less than $V_{BE}(FA)$, then the corresponding Q is off. i.e. $I_{CC} = 0$

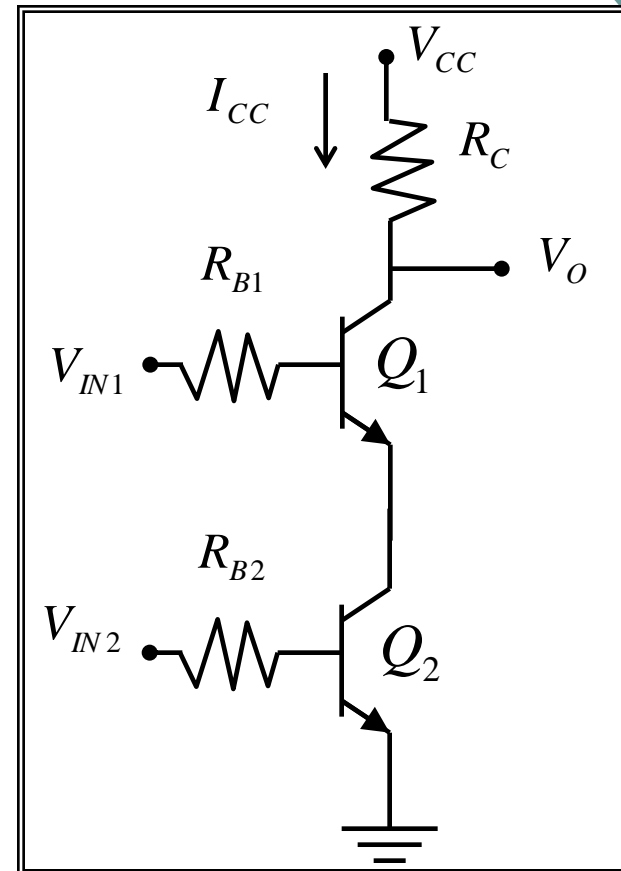
$$V_{OH} = V_{CC}$$

$$V_O = V_{CE}(sat)$$

Q_2 starts conducting (ON) if $V_{IN2} > V_{BE2}(FA)$

Q_1 starts conducting (ON) if $V_{IN1} > V_{BE1}(FA) + V_{CE2}(sat)$

If both Q_1 and Q_2 are saturated
 $V_O = 2V_{CE}(sat)$



V_O starts decreasing below V_{CC}

Multi-Input RTL NAND Gate

$$V_{OH} = V_{CC} - I_{CC}R_C$$

$$V_{OL} = \sum_{n=1}^N V_{CEn}(sat)$$

Note: Number of inputs of an RTL NAND is limited

Example

Determine the maximum fan-in for basic RTL NAND gate, assuming $V_{CE}(sat)=0.2V$, $V_{BE}(FA)=0.7V$

Solution

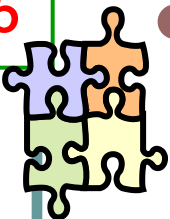
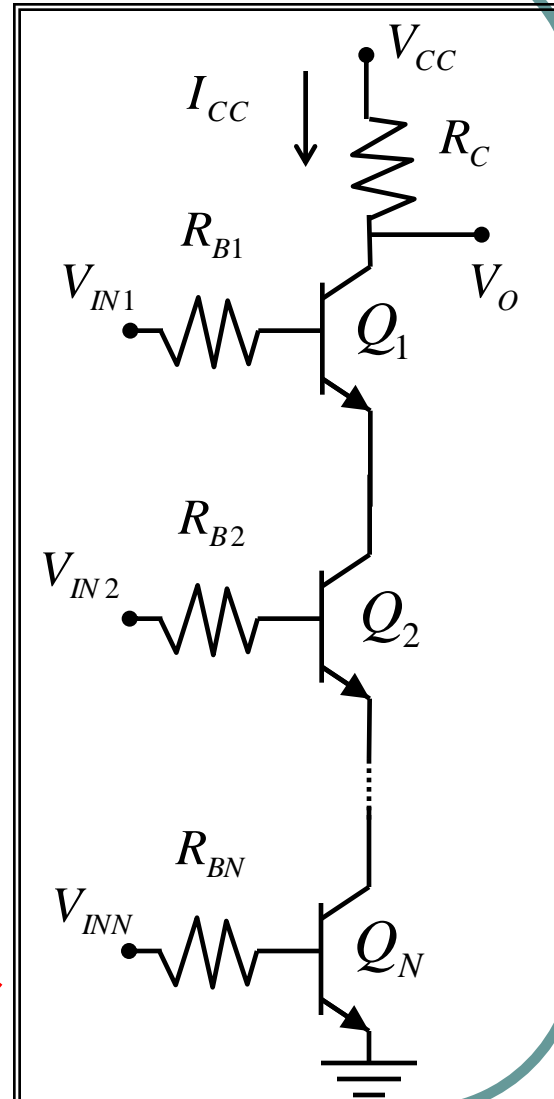
MUST $N_{ML} = V_{IL} - V_{OL} > 0$ $N_{MH} = V_{OH} - V_{IH} > 0$

$$V_{IL} > V_{OL} \Rightarrow 0.7 > N \times V_{CE}(sat) \quad \rightarrow$$

$$N < \frac{0.7}{0.2} = 3.5 \Rightarrow N = 3$$

Always valid

$$V_{OH} > V_{IH} \Rightarrow V_{CC} > V_{BE}(FA) \quad \checkmark$$



RTL Fan-Out

1 When an RTL gate is at output **low** state, then any load RTL gate will be in cut-off and draws **no** current

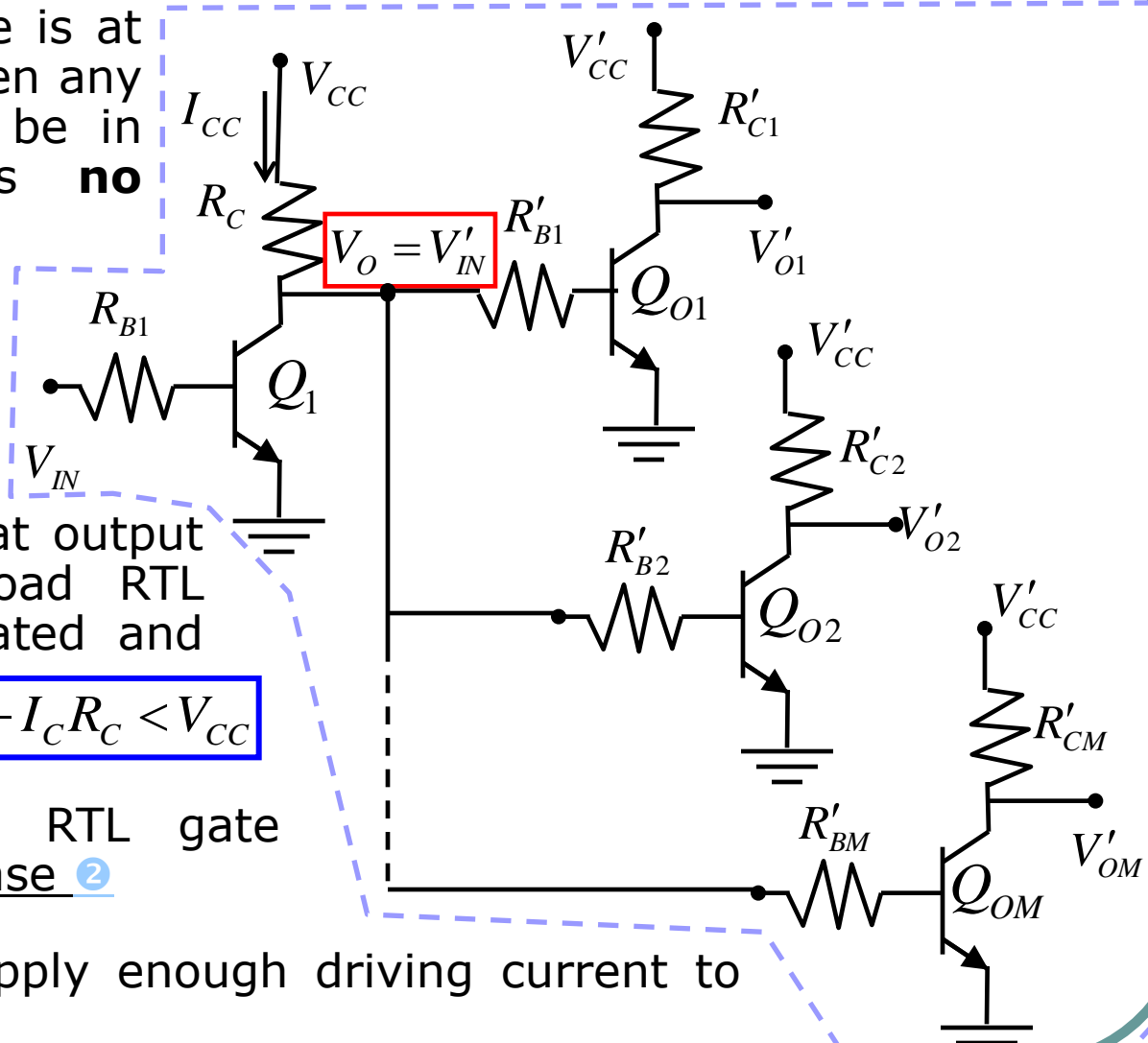
$$V_{OL} = V_{CE}(sat) = V'_{IN} < V_{BE}(FA)$$

2 When an RTL gate is at output **high** state, then all load RTL gates will be in saturated and draw current

$$V_{OH} = V_{CC} - I_C R_C < V_{CC}$$

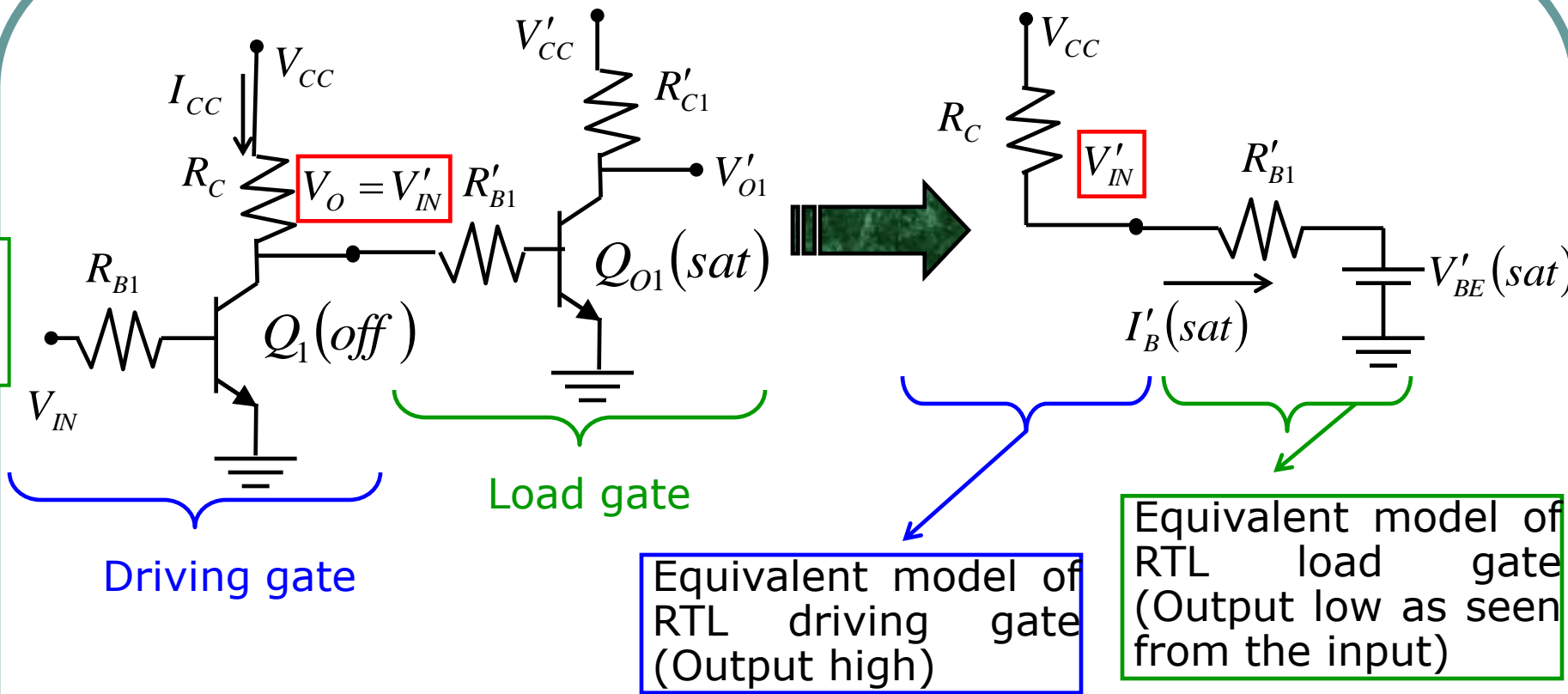
3 Maximum fan-out of RTL gate therefore depends on case 2

4 Driving gate must supply enough driving current to saturate all load gates

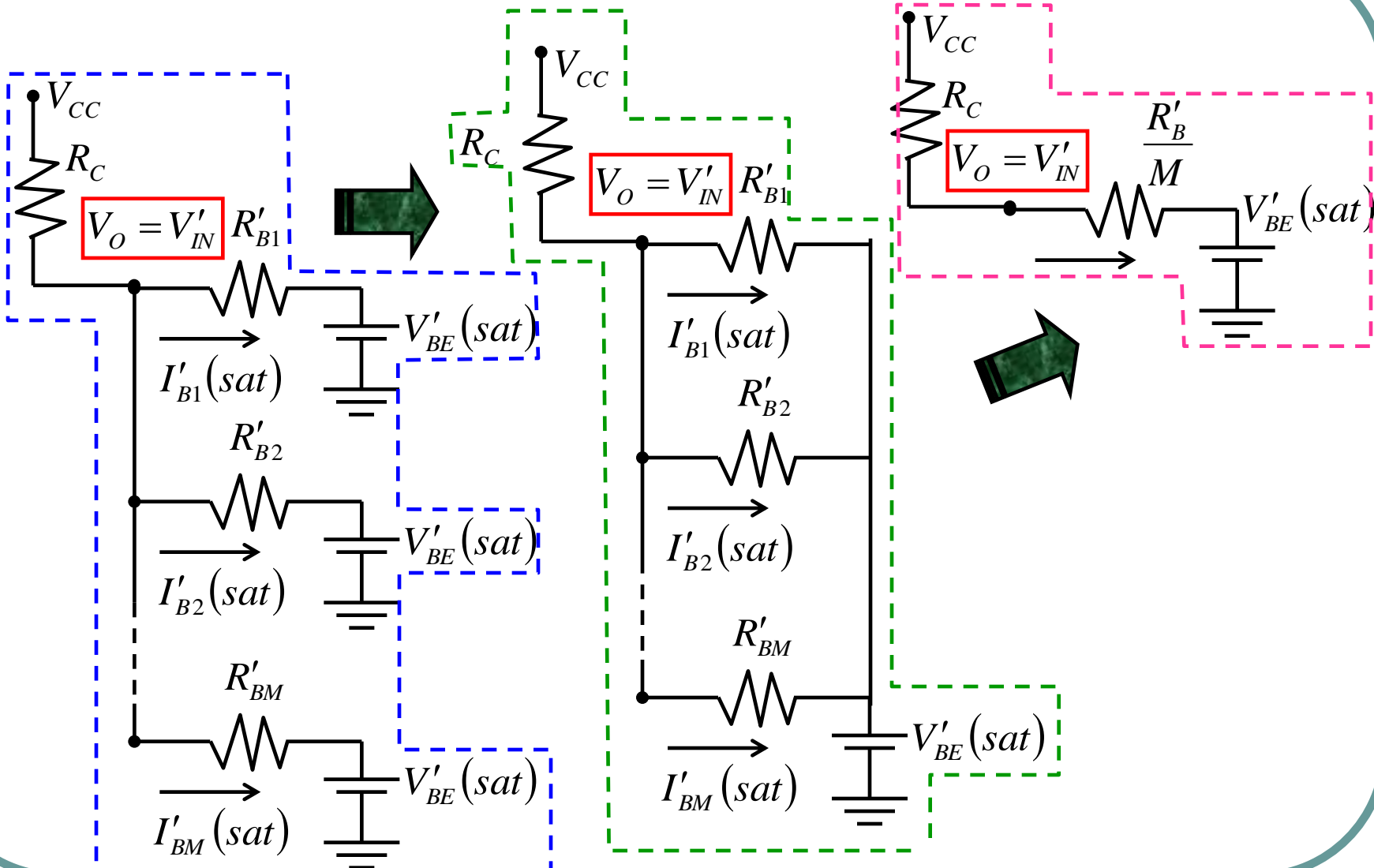


RTL Fan-Out

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RTL Fan-Out

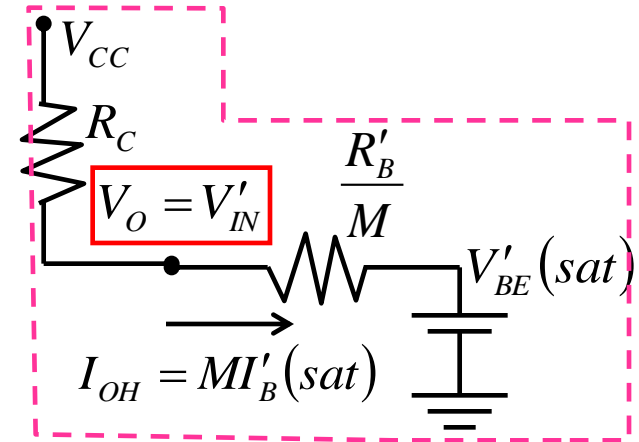


RTL Fan-Out

$$\frac{V_{CC} - V_O}{R_C} = \frac{V_O - V_{BE}(sat)}{R'_B / M}$$

$$M = \frac{(V_{CC} - V_O) / R_C}{(V_O - V_{BE}(sat)) / R'_B} \quad \star$$

$$M = \frac{I_{OH}}{I_{IH}}$$

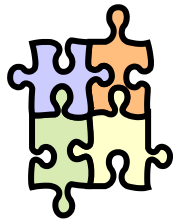


- ① As M increases, the collector current of the driving gate increases, i.e. V_{OH} decreases. V_{OH} should be large enough to saturate all load gates

$$V_{OH}(\min) = V_{IH} = \frac{V_{CC} - V_{CE}(sat)}{\beta_F R'_C} R'_B + V'_{BE}(sat) \quad \star \star \quad (\text{Proved in p. 10 of CH.4})$$

- ② Now, substituting $V_{OH}(\min)$ ($\star \star$) as V_O in (\star) gives the maximum fan-out

RTL Fan-Out



Example

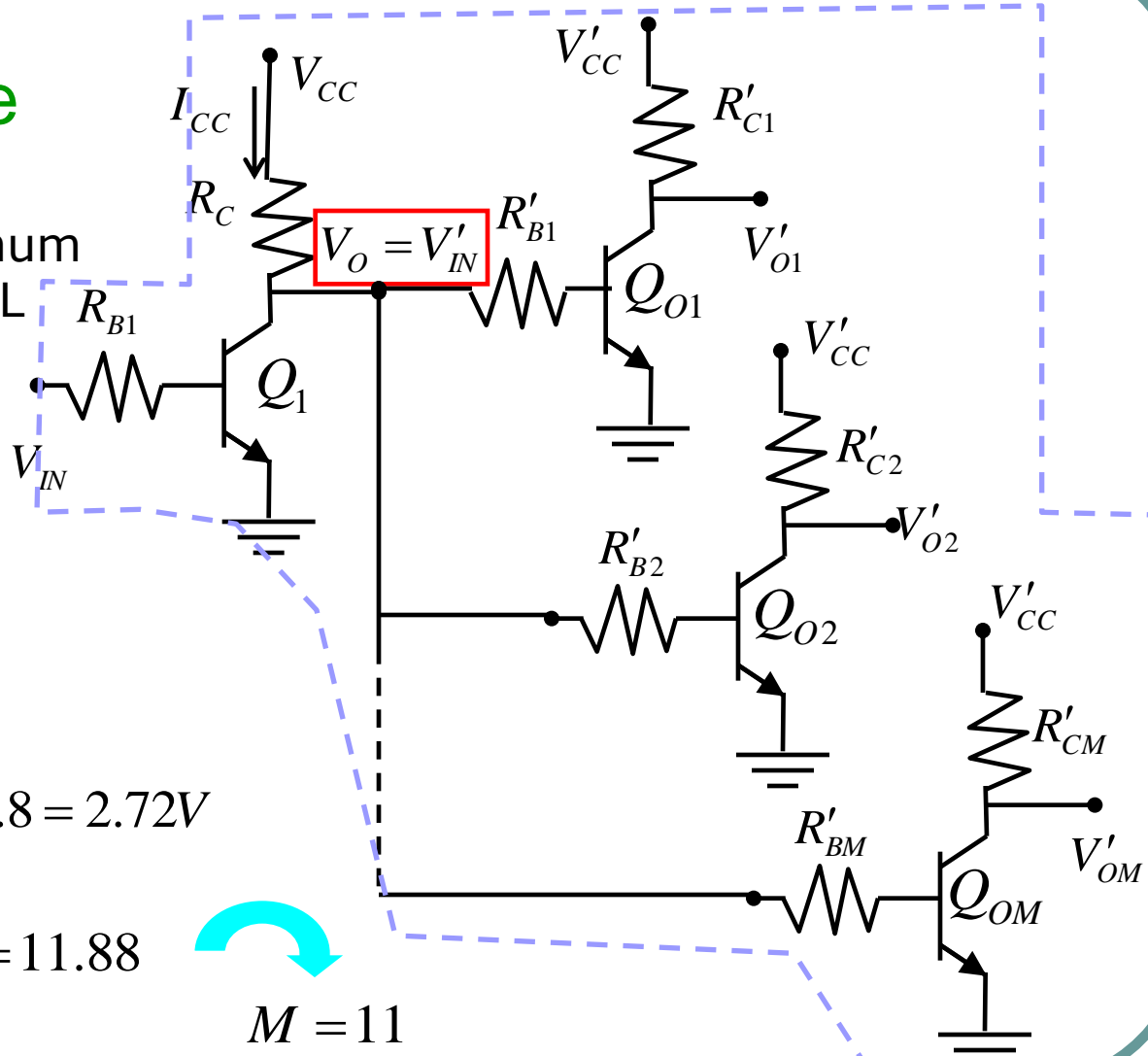
Determine the maximum fan-out for driving RTL gate, assuming $V_{CE}(\text{sat})=0.2\text{V}$, $V_{BE}(\text{sat})=0.8\text{V}$, $\beta_F=25$, $V_{CC}=5\text{V}$, $R_C=1\text{k}\Omega$, $R_B=10\text{k}\Omega$

Solution

$$V_{OH}(\text{min}) = \frac{5 - 0.2}{25} \times 10 + 0.8 = 2.72\text{V}$$

$$\text{But } M = \frac{(5 - 2.72)/1}{(2.72 - 0.8)/10} = 11.88$$

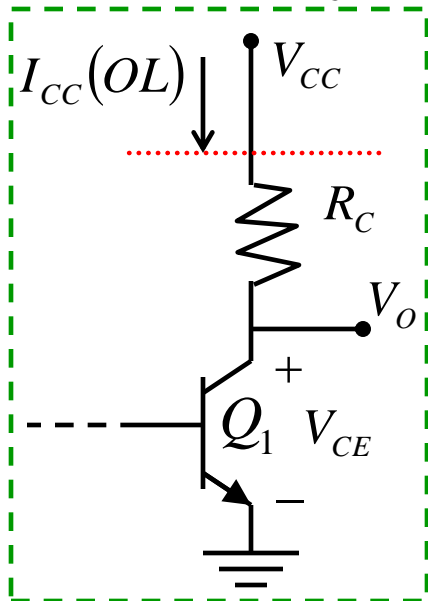
$$M = 11$$



RTL Power-Dissipation

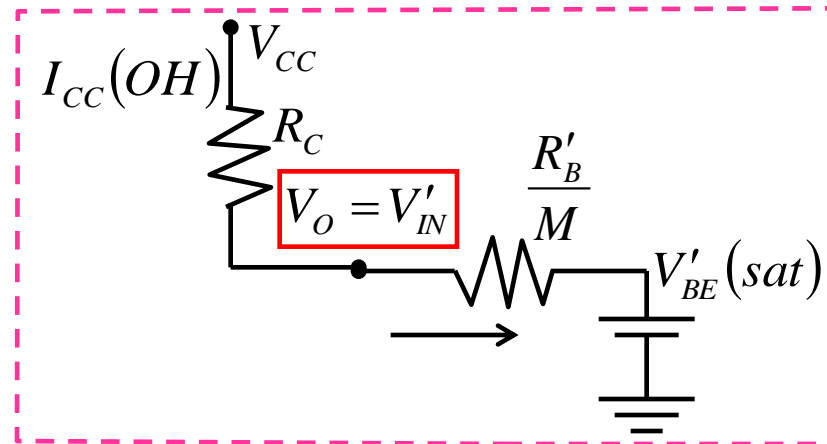
Output low supplied current
= $I_{CC}(OL)$

$$I_{CC}(OL) = \frac{V_{CC} - V_{CE}(sat)}{R_C}$$



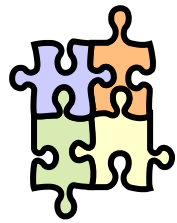
Output high supplied current
assuming M-load gates
= $I_{CC}(OH)$

$$I_{CC}(OH) = \frac{V_{CC} - V_{BE}(sat)}{R_C + \frac{R'_B}{M}}$$



$$P_{CC}(avg) = V_{CC} \left(\frac{I_{CC}(OH) + I_{CC}(OL)}{2} \right)$$

RTL Power-Dissipation



● Example

Determine the average dissipated power for

A. No load

B. Fan-out of 1

Assuming $V_{CE}(sat)=0.2V$, $V_{BE}(sat)=0.8V$, $\beta_F=25$, $V_{CC}=5V$,
 $R_C=1k\Omega$, $R_B=10k\Omega$

● Solution

A. No load:

$$I_{CC}(OL) = \frac{V_{CC} - V_{CE}(sat)}{R_C}$$
$$= \frac{5 - 0.2}{1} = 4.8mA$$

$$I_{CC}(OH) = 0mA$$

$$P_{CC}(avg) = 5 \left(\frac{4.8}{2} \right) = 12mW$$

B. $M=1$:

$$I_{CC}(OL) = \frac{V_{CC} - V_{CE}(sat)}{R_C}$$
$$= \frac{5 - 0.2}{1} = 4.8mA$$

$$I_{CC}(OH) = \frac{V_{CC} - V_{BE}(sat)}{R_C + \frac{R'_B}{M}}$$
$$= \frac{5 - 0.8}{1 + 10} = 0.382mA$$

$$P_{CC}(avg) = 5 \left(\frac{4.8 + 0.382}{2} \right)$$
$$= 12.96mW$$

Basic RTL Non-Inverter (Emitter Follower in Analog Ccts)

● Voltage-Transfer Characteristics

For $V_I - GND < V_{BE}(FA)$ \Rightarrow $I_B = 0, I_C = 0, V_O = 0 = V_{OL}$

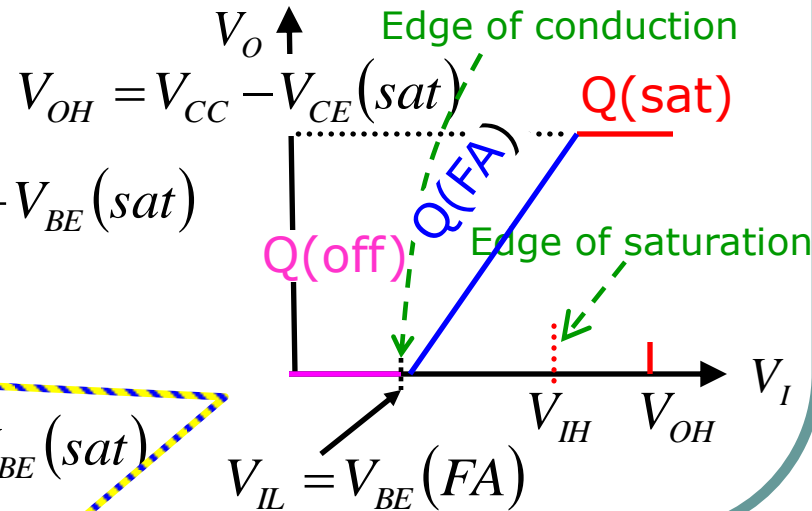
For $V_I - GND \geq V_{BE}(FA)$ \Rightarrow $I_B = (V_I - V_{BE}(FA)) / (R_B + (1 + \beta_F)R_E)$,
 $V_O = R_E (V_I - V_{BE}(FA)) / (R_B / (1 + \beta_F) + R_E)$

For $V_I - GND \geq V_{IH}$ \Rightarrow

$I_E = (V_{CC} - V_{CE}(sat)) / R_E$
 $V_O = V_{CC} - V_{CE}(sat) = V_{OH}$

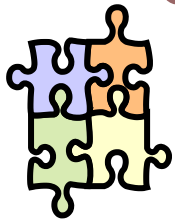
$$V_{IH} = I_B(sat)R_B + V_{BE}(sat) + I_E(sat)R_E$$

$$= I_E(EOS) \left(R_E + \frac{R_B}{(1 + \beta_F)} \right) + V_{BE}(sat)$$



$$V_{IH} = \frac{V_{CC} - V_{CE}(sat)}{R_E} \left(R_E + \frac{R_B}{(1 + \beta_F)} \right) + V_{BE}(sat)$$

BJT Non-Inverter (Basic RTL Non-Inverter)



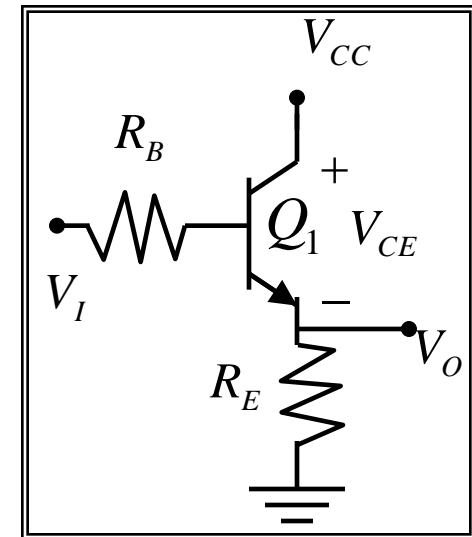
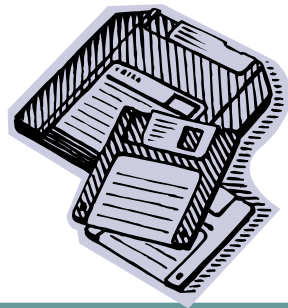
- **Example**

Assume $V_{CC} = 5\text{ V}$, $R_E = 1\text{ k}\Omega$, $R_B = 10\text{ k}\Omega$, $\beta_F = 25$;
 $V_{CE}(\text{sat}) = 0.2\text{ V}$, $V_{BE}(\text{sat}) = 0.8\text{ V}$, $V_{BE}(\text{FA}) = 0.7\text{ V}$,

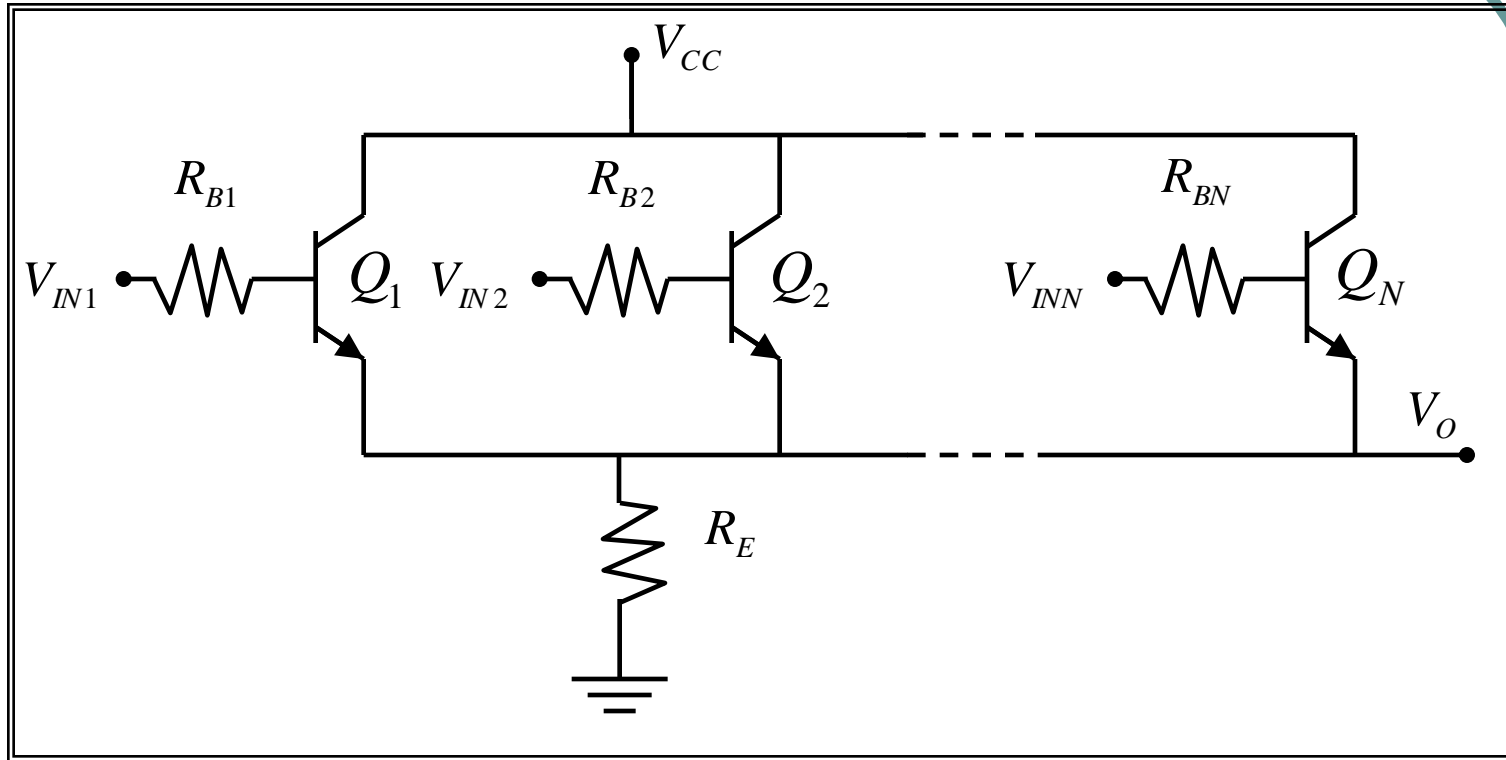
Determine the VTC parameters

- **Solution**

$$\begin{array}{ll} V_{IL} = 0.7\text{ V}, & V_{IH} = 7.45\text{ V}, \\ V_{OL} = 0.0\text{ V}, & V_{OH} = 4.8\text{ V}, \end{array}$$



Basic RTL OR Gate



If all inputs are less than $V_{BE}(FA)$ $\rightarrow V_o = 0$ Low

If at least one input is greater than V_{IH} $\rightarrow V_o = V_{CC} - V_{CE}(sat)$ High

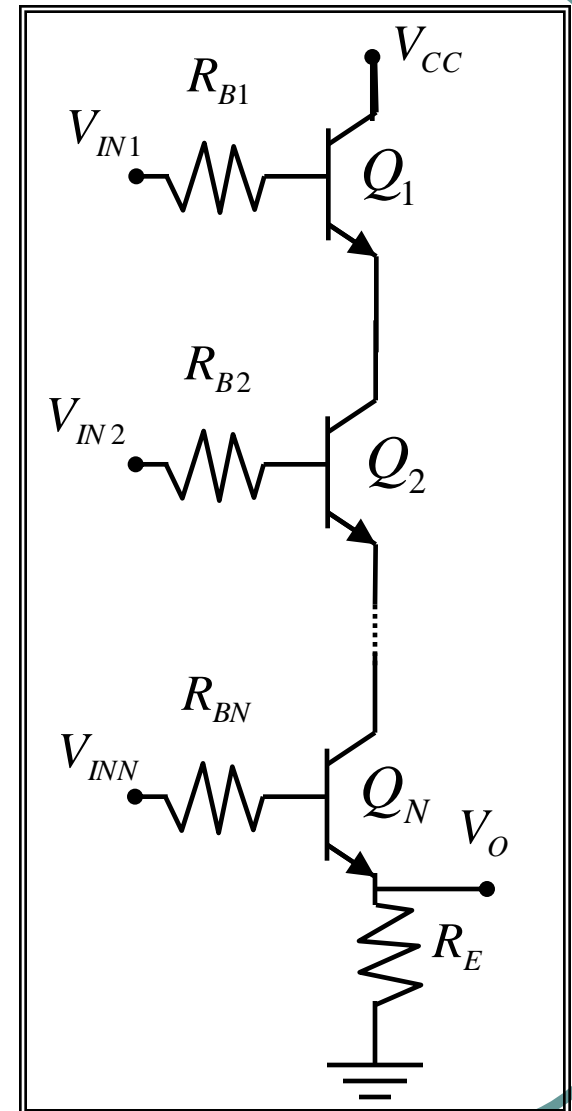
Basic RTL AND Gate

If at least one input less than $V_{BE}(FA)$, then the corresponding Q is off. i.e. $I_E = 0$

$$V_{OL} = 0$$

If ALL inputs are greater than V_{IH} , then the corresponding Q is saturated.

$$V_{OH} = V_{CC} - N \times V_{CE}(sat)$$



RTL With Active Pull-Up Inverter

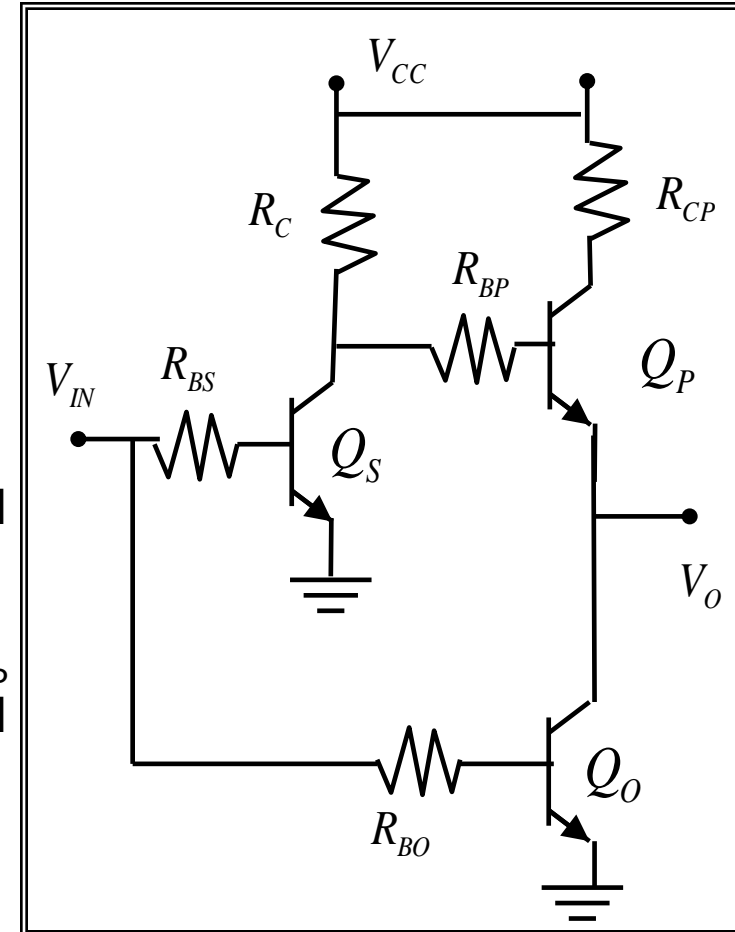
The object is to increase the fan-out of RTL inverter gate (gives more current).

To accomplish active pull-up:

Basic assumptions: * $R_{CP} \ll R_C$
 $R_{CP} \cong 0.1 \times R_C$

* $R_{BS} = R_{BO}$ and Q_O & Q_S turn ON and OFF simultaneously

* Q_S provides logic inversion for Q_P such that Q_S & Q_P never turn ON simultaneously



RTL With Active Pull-Up Inverter

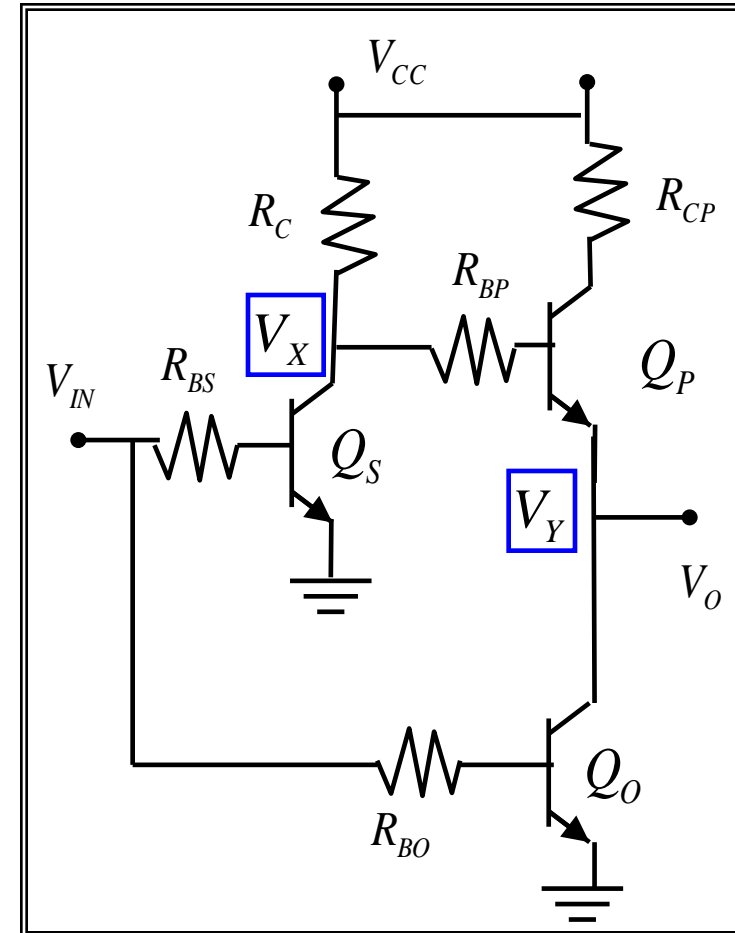
For $V_{IN} \geq V_{INH}$ (Logic High)

Q_O & Q_S are ON (sat) $V_X = V_Y = 0.2V \rightarrow$
 $V_X - V_Y < V_{BEP}(FA)$. i.e. Q_P is cut-off (very
very large resistance)

For $V_{IN} \leq V_{INL}$ (Logic Low)

Q_O & Q_S are cut-off
 Q_P is ON (sat)

$$V_O = V_{CC} - V_{CE}(sat) - I_{CP}R_{CP}$$

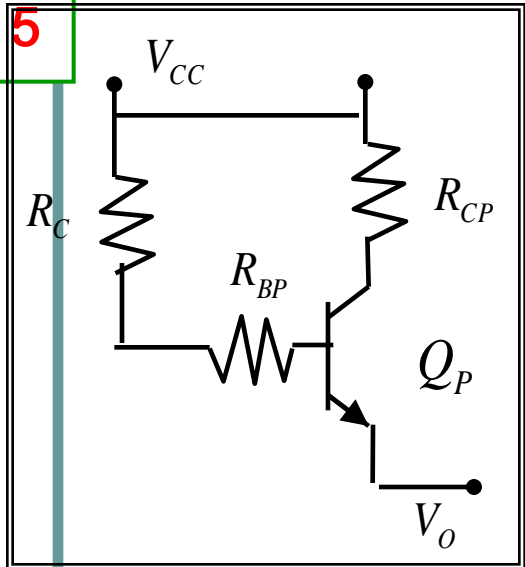


Fan-Out of RTL With Active Pull-Up Inverter

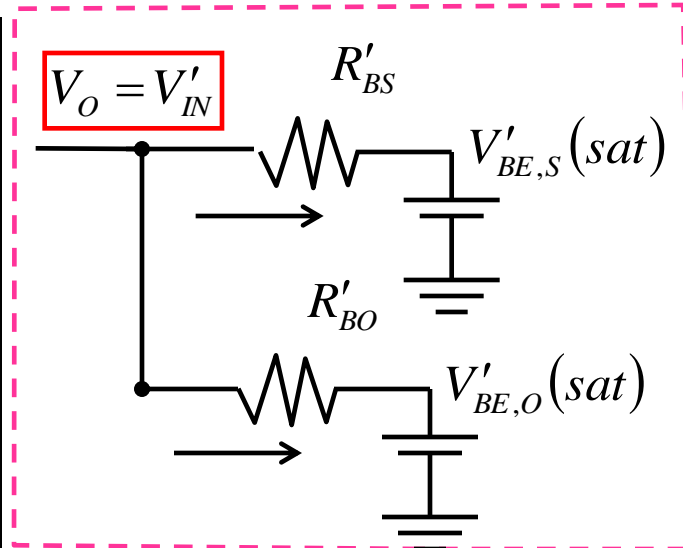
Fan-out is limited by the output high state of the driving gate

Q_O & Q_S are cut-off

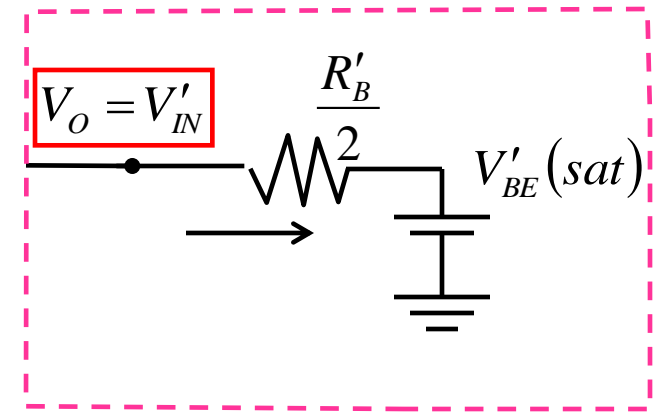
Q_P is ON (sat)



Equivalent cct of driving gate when output is high



Equivalent cct of one load gate when input is high



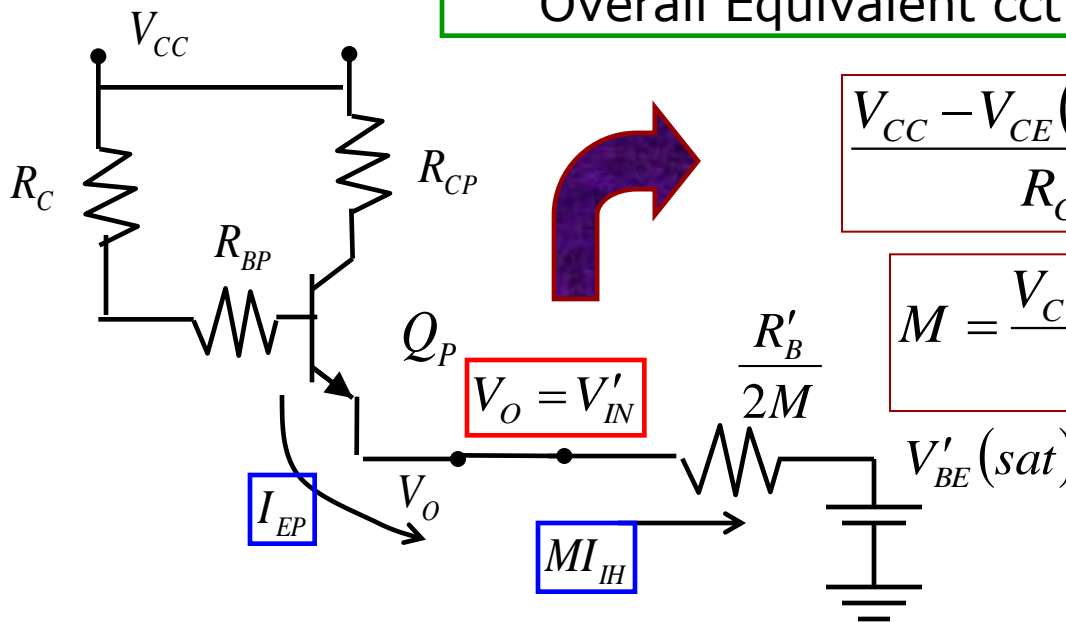
Fan-Out of RTL With Active Pull-Up Inverter

Fan-out is limited by the output high state of the driving gate

Q_O & Q_S are cut-off

Q_P is ON (sat)

Overall Equivalent cct



$$\frac{V_{CC} - V_{CE}(sat) - V_O}{R_{CP}} = \frac{V_O - V_{BE}(sat)}{R'_B/2M}$$

$$M = \frac{V_{CC} - V_{CE}(sat) - V_O}{V_O - V_{BE}(sat)} \times \frac{R'_B}{2R_{CP}}$$

As M increases, I_{EP} increases, then V_O decreases

Fan-Out of RTL With Active Pull-Up Inverter

The limiting factor for V_O is that it must be sufficient to saturate Q_S and Q_O of the load gates.

It is easy to saturate Q_S since its effective load seen by the collector is very large with negligible I_B since Q_P is cut-off

i.e. to saturate Q_S , we need:

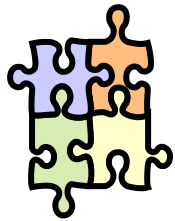
$$V_{OH}(\min) = V_{IH} = V_{BE}(sat) + \frac{R_B}{\beta_F} \left(\frac{V_{CC} - V_{CE,S}(sat)}{R_C} \right) \quad (\text{Proved also in p. 10 of CH.4})$$

Substitute in

$$M = \frac{V_{CC} - V_{CE}(sat) - V_O}{V_O - V_{BE}(sat)} \times \frac{R'_B}{2R_{CP}}$$



Fan-Out of RTL With Active Pull-Up Inverter




● Example

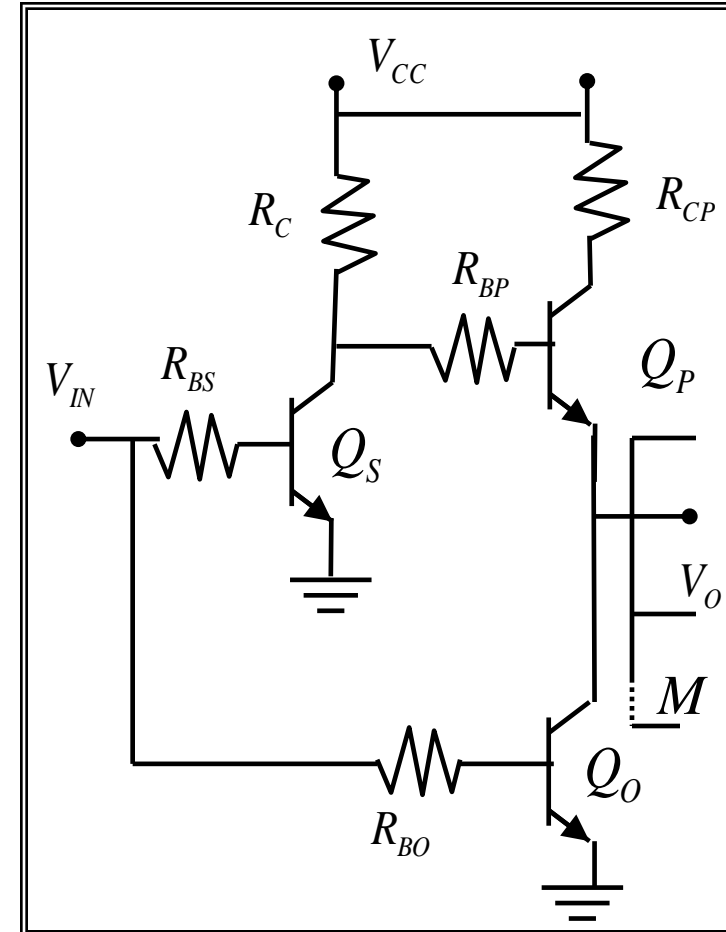
Determine the maximum **fan-out** for driving RTL gate, assuming $V_{CE}(\text{sat})=0.2\text{V}$, $V_{BE}(\text{sat})=0.8\text{V}$, $\beta_F=25$, $V_{CC}=5\text{V}$, $R_C=1\text{k}\Omega$, $R_{BO}=R_{BS}=10\text{k}\Omega$, $R_{CP}=100\Omega$.

● Solution

$$V_{OH}(\text{min}) = 0.8 + \frac{10}{25} \left(\frac{5 - 0.2}{1} \right) = 2.7\text{V}$$

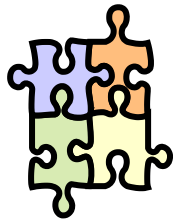
$$M = \frac{5 - 0.2 - 2.7}{2.7 - 0.8} \times \frac{10}{2 \times 0.1} = 55.3$$


$$M = 55$$



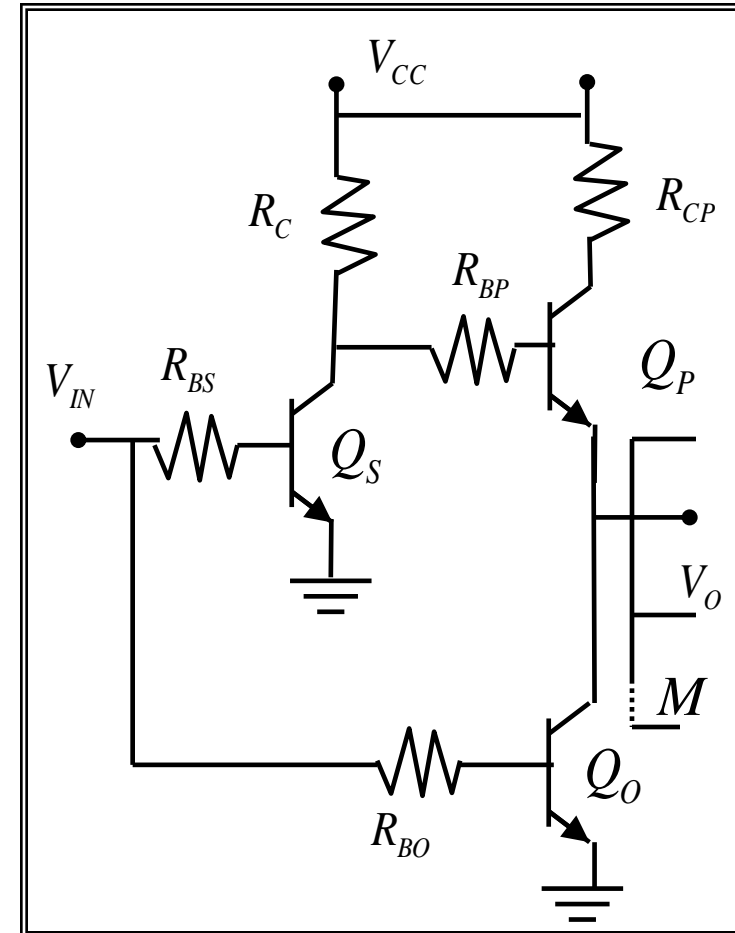
(without pull-up, M was 11. i.e. It increases 500%. See p. 10)

RTL SPICE Simulation



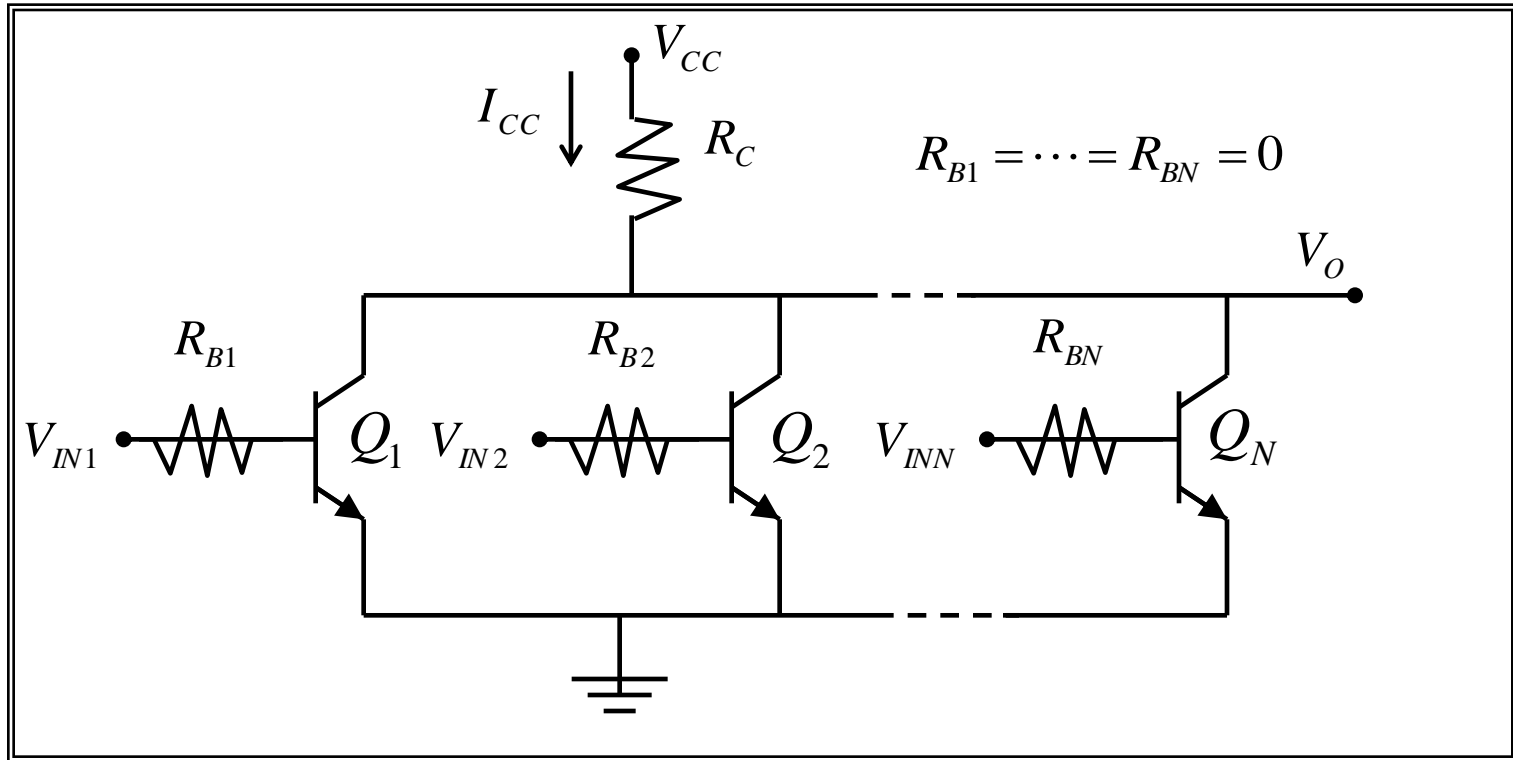
● Example

- *Repeat the last example using PSPICE
- *Plot V_O as a function of V_{IN}
- *Refer to pages 67-68 in the text book.



Direct Coupled Transistor Logic

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Ch 5



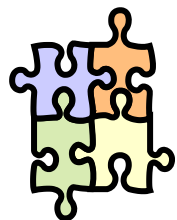
Three-input DCTL NOR gate

Advantage: Reduce the packing density of RTL in integrated circuits form since the base resistors are eliminated

Disadvantage: Current hogging when V_o is at logic high for fan-out greater than one



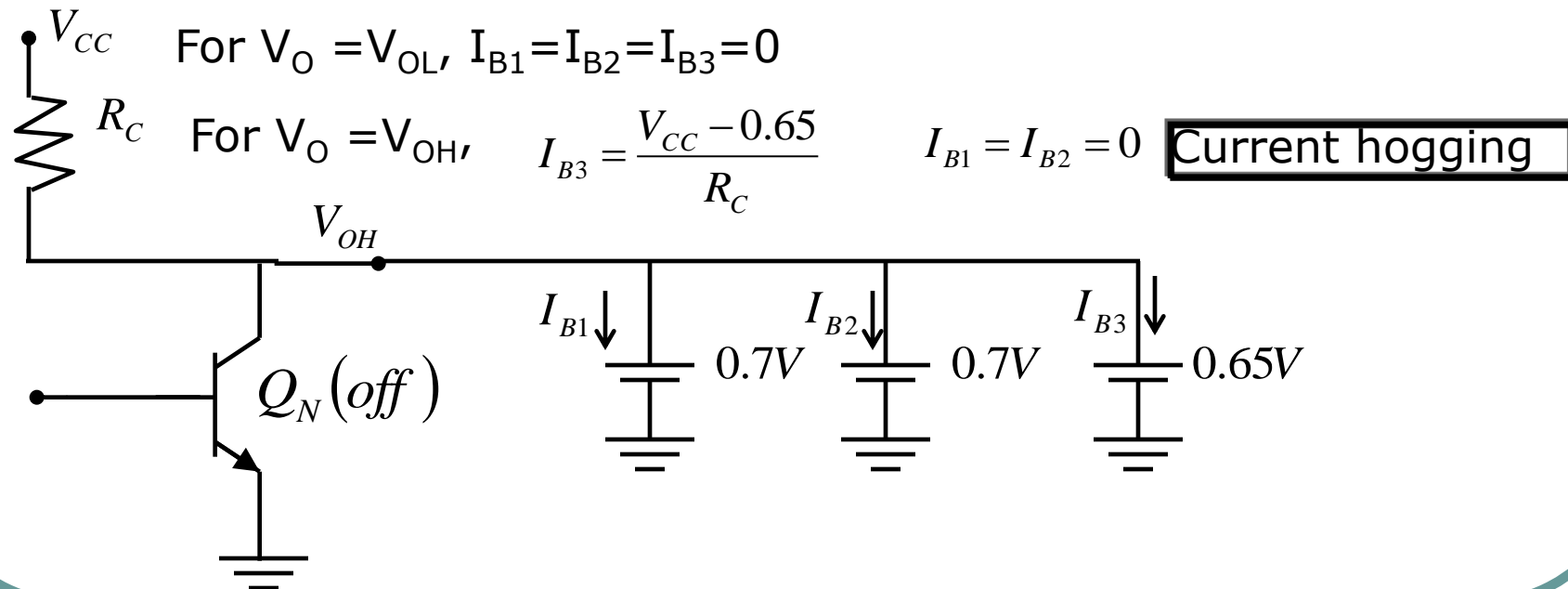
Direct Coupled Transistor Logic



● Example

Consider a DCTL RTL inverter with fan-out be three with $V_{BE1}(FA)=0.7V$, $V_{BE2}(FA)=0.7V$, $V_{BE3}(FA)=0.65V$. Determine the base current of each load gate for output high state.

● Solution



- HW #5: Solve Problems: 5.8, 5.11, 5.22, 5.24, 5.27, 5.28, 5.29 (hint: neglect I_{BP})

- *Solutions of Prob. 5.24 & 5.27:
On the white board*